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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Seamus Paul Whiston et al
Serial No: 09/480,223
Confirmation No.: 4079
Filed: January 10, 2000
For: METHOD FOR FORMING A DMOS DEVICE AND A DMOS DEVICE

Examiner: Huynh, Yennhu B.
Art Unit: 2813

#13/Reg for
Reconsideration
(NE)
5/7/03
Adm 1/2

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COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

Sir:

REQUEST FOR RECONSIDERATION

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In response to the Final Action mailed October, 2002, Applicant requests reconsideration of the obviousness rejections under §103, for the reasons detailed below.

REMARKS

Briefly, none of the prior art references discloses the formation of a body region in a DMOS device -- or, indeed, in any other device in which the body region is formed by steps (a) and (b) of claim 1.

The principal reference is Hshieh '408. Hshieh discloses a method performing a body region 64 in a DMOS device. In general, it is directed toward a vertical DMOS (the DMOS device), but Hshieh does suggest that his methods also be used in the fabrication of a lateral DMOS (LDMOS) device. In a vertical DMOS, the current flows vertically from the top to the bottom, while in a lateral DMOS the current flows laterally. The DMOS described in the specification of the present application is a lateral DMOS. However, Applicant does not wish to limit claim 1 to an LDMOS. In the specification at page 13, lines 13-20, we have described other DMOS devices which could be fabricated using the disclosed method, one of which is a vertical DMOS.